

IN THE SPECIFICATION:

Please amend page 15, last paragraph (continuing to page 16) as follows:

As shown in Figs. 1, 4 and 5, the power MOSFET device, indicated at 1, has a flat quadrangular sealing member (package) 2 formed of an insulating resin[[?]]. A source electrode terminal 4, a gate electrode terminal 5 and drain electrode terminals 6, serving as external electrode terminals, are positioned on a lower surface 3 of the sealing member 2 in such a manner that respective lower surfaces are exposed. As shown in Fig. 5, the source electrode terminal 4, the gate electrode terminal 5 and the drain electrode terminals 6 project slight (for example, about 0.1 to 0.2 mm) from side faces 7 of the sealing member 6. Thus, the power MOSFET device 1 has a so-called non-lead structure.